

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A Group III nitride semiconductor light-emitting device comprising:

a stacked structure formed on a crystal substrate ~~to be removed from it~~, removable from the stacked structure, and including two Group III nitride semiconductor layers having different electric conductive types and a light-emitting layer which is stacked between the two Group III nitride semiconductor layers and which comprises a Group III nitride semiconductor; and

a plate body made of material different from that of the crystal substrate and formed on a surface of an uppermost layer which is opposite from the crystal substrate that is ~~removed~~ removable from the stacked structure,

wherein the crystal substrate is a sapphire substrate having a (0001) face on which the stacked structure is formed, the plate body is a conductive (001) -Si monocrystal, and

wherein the plate body has a <110> crystal orientation that is in parallel to a [1.1 . -2.0] crystal orientation of the (0001)-sapphire substrate.

2. (original): The Group III nitride semiconductor light-emitting device according to claim 1, wherein the plate body is made of conductive material.

3. (previously presented): The Group III nitride semiconductor light-emitting device according to claim 1, wherein the crystal substrate is removed from the stacked structure by irradiating laser beams onto a junction interface region between the stacked structure and the crystal substrate.

4. (previously presented): The Group III nitride semiconductor light-emitting device according to claim 1, further comprising an ohmic electrode provided on the plate body.

5. (previously presented): The Group III nitride semiconductor light-emitting device according to claim 1, wherein the plate body is formed on the surface of the uppermost layer through a metal layer.

6. (original): The Group III nitride semiconductor light-emitting device according to claim 5, wherein the metal layer comprises eutectic metal film.

7. (previously presented): The Group III nitride semiconductor light-emitting device according to claim 1, further comprising a metal reflection film for reflecting light from the light-emitting layer provided between the plate body and the surface of the uppermost layer.

8. (canceled).

9. (canceled).

10. (withdrawn-currently amended): A method of producing a Group III nitride semiconductor light-emitting device comprising:

a stacked structure formed on a crystal substrate removable from the stacked structure, and including two Group III nitride semiconductor layers having different electric conductive types and a light-emitting layer which is stacked between the two Group III nitride semiconductor layers and which comprises a Group III nitride semiconductor; and

a plate body made of material different from that of the crystal substrate and formed on a surface of an uppermost layer which is opposite from the crystal substrate that is removable from the stacked structure,

wherein the crystal substrate is a sapphire substrate having a (0001) face on which the stacked structure is formed, the plate body is a conductive (001) -Si monocrystal, and

wherein the plate body has a $\langle 110 \rangle$ crystal orientation that is in parallel to a $[1.1 \ . \ -2.0)$ crystal orientation of the (0001)-sapphire substrate,

said method comprising the steps of:

forming on a crystal substrate to be removed a stacked structure including two Group III nitride semiconductor layers having different electric conductive types and a light-emitting layer which is stacked between the two Group III nitride semiconductor layers and which comprises a Group III nitride semiconductor;

forming a plate body made of material different from that of the crystal substrate on a surface of an uppermost layer which is opposite from the crystal substrate; and

removing the crystal substrate.

11. (canceled).